

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A nitride semiconductor laser device comprising a nitride semiconductor substrate (101); a nitride semiconductor layer that has an n-type semiconductor layer (102), an active layer (104) and a p-type semiconductor layer (103) laminated on or above the nitride semiconductor substrate (101), and has a stripe-shaped waveguide region for laser light; and end surface protective films (108, 109) on the both end surface of resonance sandwiching ~~substantially perpendicular~~ to the waveguide region, wherein

the nitride semiconductor substrate (101) has a luminescent radiation region (112) that absorbs light emitted from the active layer (104) and emits luminescent radiation with a wavelength longer than the wavelength of the emitted light, and

at least one of the end surface protective films (108, 109) have a high reflectivity for the wavelength of the luminescent radiation from the luminescent radiation region (112).

2. (Original) The nitride semiconductor laser device according to claim 1, wherein the end surface protective films (108, 109) are located on the end surfaces both on the emission side and the rear side.

3. (Original) The nitride semiconductor laser device according to claim 1, wherein the end surface protective films (108, 109) have a low reflectivity for the wavelength of the emitted light from the active layer (104).

4. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 3~~ claim 1, wherein the end surface protective films (108, 109) have a single-layer or multilayer structure.

5. (Currently Amended) A nitride semiconductor laser device comprising a nitride semiconductor substrate (101); a nitride semiconductor layer that has an n-type semiconductor layer (102), an active layer (104) and a p-type semiconductor layer (103) laminated on or above the nitride semiconductor substrate (101), and has a stripe-shaped waveguide region for laser light; and an emission-side end surface protective film and a rear-side end surface protective film opposed thereto on the end surfaces resonance sandwiching ~~substantially perpendicular~~ to the waveguide region, wherein

the nitride semiconductor substrate (101) has a luminescent radiation region (112) that absorbs light emitted from the active layer (104) and emits luminescent radiation with a wavelength longer than the wavelength of the emitted light, and

the rear-side end surface protective film includes a first end surface protective film having a high reflectivity for the wavelength of the luminescent radiation, and a second end surface protective film having a high reflectivity for the wavelength of the emitted light from the active layer (104), wherein

the emission-side end surface protective film includes a third end surface protective film having a high reflectivity for the wavelength of the luminescent radiation.

6. (Original) The nitride semiconductor laser device according to claim 5, wherein the first end surface protective film and/or the third end surface protective film has a low reflectivity for the wavelength of the emitted light from the active layer (104).

7. (Currently Amended) The nitride semiconductor laser device according to claim 5 ~~or~~ 6, wherein the emission-side end surface protective film includes a fourth end surface protective film having a high reflectivity for the wavelength of the emitted light from the active layer (104).

8. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 5 to 7~~ claim 7, wherein each of the first, second, third and fourth end surface protective films (108, 109) has a single-layer or multilayer structure.

9. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 5 to 8~~ claim 5, wherein the first and second end surface protective films are laminated so as to at least partially overlap each other.

10. (Currently Amended) The nitride semiconductor laser device according to claim 8, wherein the third and fourth end surface protective films are laminated so as to at least partially overlap each other.

11. (Currently Amended) The nitride semiconductor laser device according to claim 5 ~~or 6~~, wherein the second end surface protective film is formed in contact with the nitride semiconductor layer.

12. (Currently Amended) The nitride semiconductor laser device according to claim 7, wherein the fourth end surface protective film is formed in contact with the nitride semiconductor layer.

13. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 12~~ claim 1, wherein the luminescent radiation region (112) has a low dislocation density as compared with the periphery thereof.

14. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 13~~ claim 1, wherein the luminescent radiation region (112) has a high impurity concentration as compared with the periphery thereof.

15. (Original) The nitride semiconductor laser device according to claim 14, wherein the impurity is at least one element selected from the group consisting of H, O, C and Si.

16. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 15~~ claim 1, wherein the active layer (104) has a light emission wavelength of 390 to 420 nm.

17. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 16~~ claim 1, wherein the luminescent radiation has a wavelength of 550 to 600 nm.

18. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 17~~ claim 1, wherein the luminescent radiation region (112) is formed in a stripe shape substantially parallel to the waveguide region.

19. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 18~~ claim 1, wherein the waveguide region is formed above the luminescent radiation region (112).

20. (Currently Amended) The nitride semiconductor laser device according to ~~any of claims 1 to 19~~ claim 1, wherein the waveguide region is formed in a region that is spaced away from the luminescent radiation region (112).

21. (Currently Amended) A laser apparatus comprising the nitride semiconductor laser device according to ~~any of claims 1 to 20~~ claim 1, and a detector that detect the light emission of the nitride semiconductor laser device, wherein the detector has a spectral sensitivity in a wavelength λ_{ex} of the luminescent radiation higher than a wavelength λ_{LD} of the emitted light of the nitride semiconductor laser device.

22. (New) A laser apparatus comprising the nitride semiconductor laser device according to claim 5, and a detector that detect the light emission of the nitride semiconductor laser device, wherein the detector has a spectral sensitivity in a wavelength λ_{ex} of the luminescent radiation higher than a wavelength λ_{LD} of the emitted light of the nitride semiconductor laser device.